

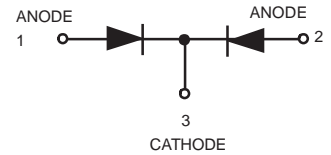
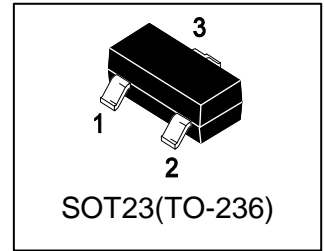
# LDAN202KLT1G

## S-LDAN202KLT1G

Dual Serise Switching Diodes

### 1. FEATURES

- Ultra high speed switching
- Suitable for high packing density layout.
- High reliability.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.



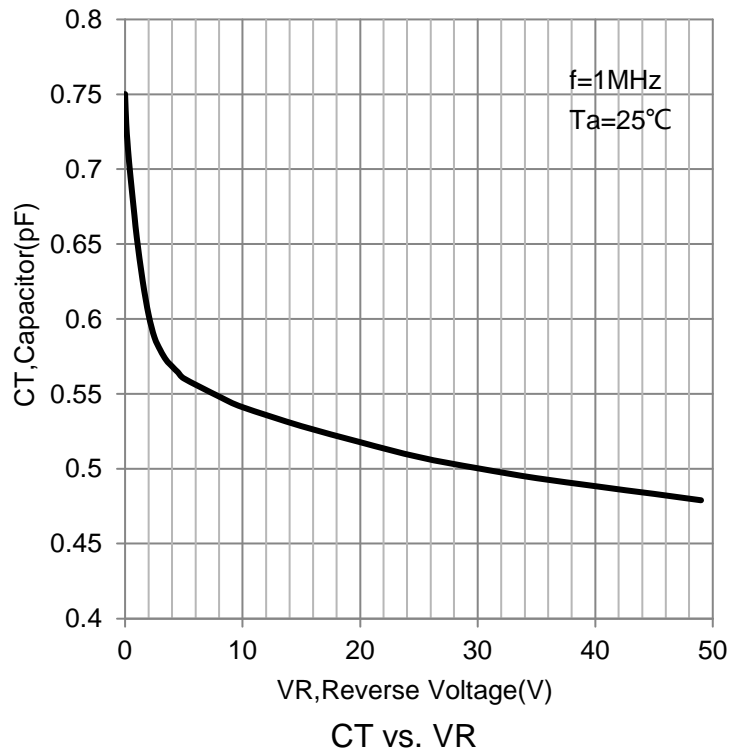
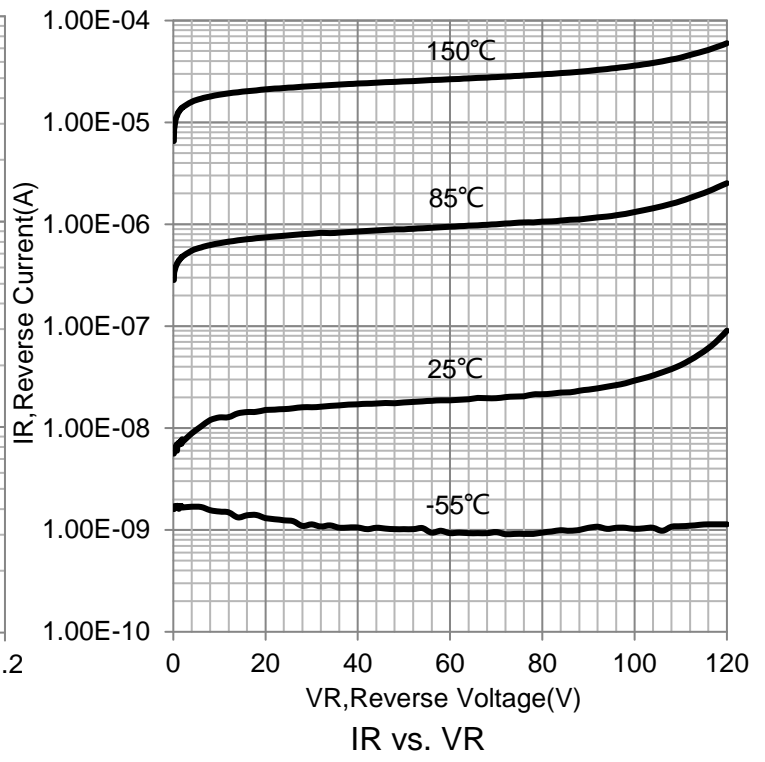
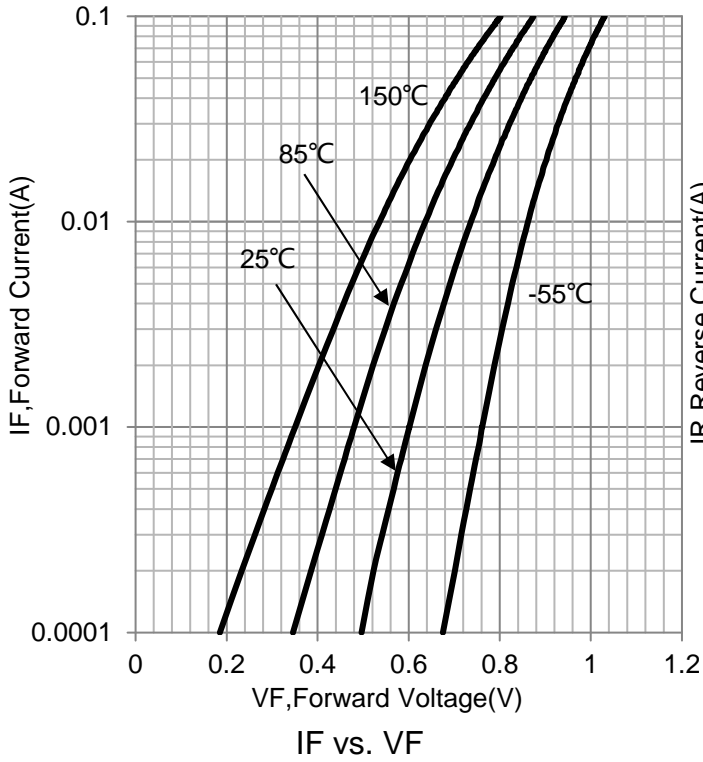
### 2. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
LDAN202KLT1G	N	3000/Tape&Reel
LDAN202KLT3G	N	10000/Tape&Reel

### 3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Reverse Voltage	VR	80	V
Forward Current	IO	100	mA
Peak Forward Surge Current	IFSM	300	mA
Forward voltage (If = 100mA)	VF	1.2	V
Reverse current (Vr = 70V)	IR	0.1	μA
Capacitance between terminals(f =1MHz)	CT	3.5	pF
Reverse recovery time(Vr= 6V,If=5 mA)	Trr	4	nS
Operating Junction and Storage temperature range	TJ,Tstg	-55~+150	°C

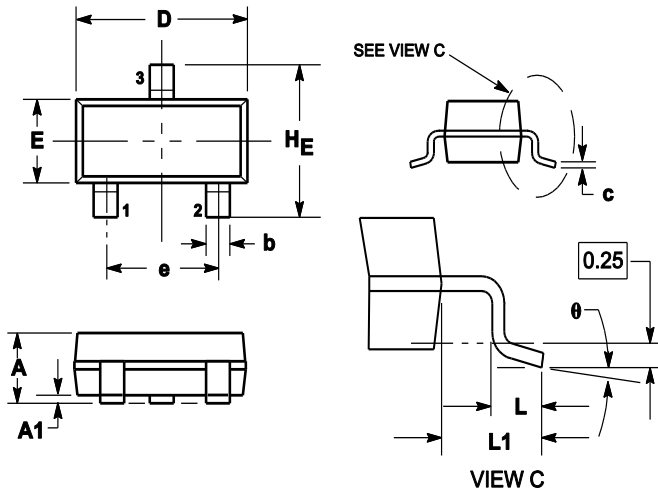
**4.ELECTRICAL CHARACTERISTICS CURVES**



### 5.OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

### 6.SOLDERING FOOTPRINT

